

Generation of a shallow donor after 6, 15 and 900 MeV electron irradiation

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This work focuses on the generation of the shallow donor level E30K after 6, 15 and 900 MeV electron irradiation in n-type FZ diodes. The E30K is known to be a cluster related defect which plays a key role in the understanding of non-type inversion of epitaxial diodes after high proton fluences. We found that the generation of E30K is suppressed for increasing electron energies. This suggests a more point like character of the defect.

Defect concentrations were obtained by means of thermally stimulated current technique for several electron fluences.

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